

Appl. No.: 10/623,815
Amdt. Dated December 23, 2005
Reply to Office action of October 28, 2005

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of claims:

Claim 1 (currently amended). A semiconductor component comprising:

a semiconductor chip including an electronic circuit configured in said semiconductor chip, said electronic circuit having a terminal for a signal to be processed, a stage connected to said terminal for the signal, a terminal for obtaining a supply potential, said terminal for obtaining the supply potential being connected to said stage, said stage being selected from a group consisting of an input stage and an output stage;

a first conductor track running outside said semiconductor chip, said first conductor track being connected to said terminal for the signal;

a second conductor track running outside said semiconductor chip, said second conductor track being connected to said terminal for obtaining the supply potential;

Appl. No.: 10/623,815
Amdt. Dated December 23, 2005
Reply to Office action of October 28, 2005

a further conductor track running outside the entire components/circuits/stages of said semiconductor chip, said further conductor track being connected to said second conductor track, said further conductor track surrounding said semiconductor chip, said further conductor track crossing said first conductor track, defining a crossing location, and said further conductor track crossing said second conductor track; and

an electrostatic discharge protection element for carrying an electrostatic discharge away from said terminal for the signal and to the supply potential, said electrostatic discharge protection element being disposed outside of said semiconductor chip, said electrostatic discharge protection element being connected outside of said semiconductor chip to said further conductor track and to said first conductor track, said electrostatic discharge protection element being disposed close to said crossing location.

Claim 2 (previously presented). The semiconductor component according to claim 1, further comprising:

a package surrounding said semiconductor chip and said further conductor track;

Appl. No.: 10/623,815
Amtd. Dated December 23, 2005
Reply to Office action of October 28, 2005

said package partially surrounding said first conductor track such that a portion of said first conductor track facing toward said semiconductor chip runs inside said package and a portion of said first conductor track facing away from said semiconductor chip runs outside said package; and

said package partially surrounding said second conductor track such that a portion of said second conductor track facing toward said semiconductor chip runs inside said package and a portion of said second conductor track facing away from said semiconductor chip runs outside said package.

Claim 3 (previously presented). The semiconductor component according to claim 1, wherein:

said electrostatic discharge protection element is a diode;

said diode has an anode connected to said further conductor track; and

said diode has a cathode connected to said first conductor track.

Claim 4 (cancelled).

Applic. No.: 10/623,815
Amdt. Dated December 23, 2005
Reply to Office action of October 28, 2005

Claim 5 (original). The semiconductor component according to claim 4, further comprising an insulation material configured where said further conductor track crosses said first conductor track.

Claim 6 (previously presented). The semiconductor component according to claim 1, further comprising:

a third conductor track;

a terminal for a signal and assigned to said third conductor track; and

a further electrostatic discharge protection element;

said further conductor track running in a main direction and having a conductor track portion branching away from said main direction;

said third conductor track crossing said further conductor track near said conductor track portion of said further conductor track, defining a further crossing location; and

Applic. No.: 10/623,815
Amdt. Dated December 23, 2005
Reply to Office action of October 28, 2005

said conductor track portion of said further conductor track is connected to said further electrostatic discharge protection element.

Claim 7 (original). The semiconductor component according to claim 1, further comprising:

a bonding wire connecting said first conductor track to said terminal for the signal; and

a bonding wire connecting said second conductor track to said terminal for obtaining the supply potential.

Claim 8 (previously presented). The semiconductor component according to claim 7, wherein said terminal for the signal and said terminal for obtaining the supply potential are metallized areas configured in said semiconductor chip.

Claim 9 (original). The semiconductor component according to claim 1, wherein:

said input stage has at least one transistor with a gate connected to said terminal for the signal;

said transistor has a drain terminal and a source terminal;

Appl. No.: 10/623,815
Amdt. Dated December 23, 2005
Reply to Office action of October 28, 2005

said drain terminal or said source terminal of said transistor connected to said terminal for the supply potential.

Claim 10 (original). The semiconductor component according to claim 9, wherein said input stage is an inverter.

Claim 11 (previously presented). The semiconductor component according to claim 1, further comprising a leadframe disposed outside said semiconductor chip and including said first conductor track, said first conductor track having a contact area connected to a terminal of said electrostatic discharge protection element.

Claim 12 (previously presented). The semiconductor component according to claim 1, wherein said first conductor track is connected to said terminal for the signal through a bonding wire.

Claim 13 (previously presented). The semiconductor component according to claim 6, wherein said further electrostatic discharge protection element is disposed at said further crossing location.